
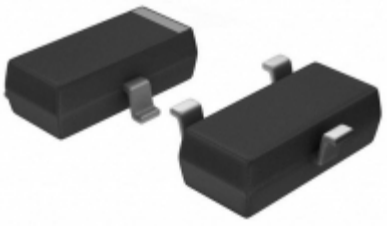
	<p>SI2343DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2343DS-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 3.1A SOT-23</p> <p>Datenblätter:  SI2343DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 91605 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2343DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 30V 3.1A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	91605 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	P-Channel 30V 3.1A (Ta) 750mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.1A (Ta)
Rds On (Max) @ Id, Vgs	53 mOhm @ 4A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	540pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Verpackung	Original-Reel®
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2343DS-T1-GE3DKR

SI2343DS-T1-GE3 ist neu im Original, Suche SI2343DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2343DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2343DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2343DS AOS SI2343DS AOS</p>	 <p>SI2347DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 5A SOT-23</p>	 <p>SI2347DS-T1-E3 VISHAY SI2347DS-T1-E3 VISHAY</p>	 <p>SI2344DS-E3 VISHAY SI2344DS-E3 VISHAY</p>
 <p>SI2347DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 5A SOT-23</p>	 <p>SI2343DS-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 3.1A SOT23-3</p>	 <p>SI2343DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 3.1A SOT23-3</p>	 <p>SI2343DS-T1 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 3.1A SOT23</p>

heiße Teile

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|-------------------|--------------------|--------------------|--------------------|-------------------|
| ⊛ SI2336DS-T1-GE3 | ↔ SI2336DS-T1-GE3 | ⇒ SI2337DS | D SI2337DS-T1-E3 | ↔ SI2337DS-T1-E3 |
| ⊣ SI2337DS-T1-GE3 | ⊛ SI2337DS-T1-GE3 | D SI2338DS-T1-E3 | ⇒ SI2338DS-T1-GE3 | ↔ SI2338DS-T1-GE3 |
| ⊛ SI2341DS | ⊣ SI2341DS-T1-E3 | ⊛ SI2341DS-T1-E3 | ↔ SI2341DS-T1-GE3 | ↔ SI2341DS-T1-GE3 |
| D SI2342DS-T1-E3 | ⊛ SI2342DS-T1-GE3 | ⊣ SI2342DS-T1-GE3 | ⊛ SI2343ADS-T1-GE3 | ↔ SI2343CDS |
| ⇒ SI2343CDS-T1-E3 | ↔ SI2343CDS-T1-GE3 | ⊛ SI2343CDS-T1-GE3 | ⊣ SI2343DS-T1-E3 | ↔ SI2343DS-T1-E3 |
| ↔ SI2343DS-T1-GE3 | ⇒ SI2344DS-E3 | D SI2347DS-T1-GE3 | ⊛ SI2347DS-T1-GE3 | ⊣ SI2351DS-T1-E3 |
| ⊛ SI2351DS-T1-E3 | D SI2351DS-T1-GE3 | ⇒ SI2351DS-T1-GE3 | ↔ SI2356DS-T1-GE3 | ↔ SI2356DS-T1-GE3 |
| ⊣ SI2365EDS | ⊛ SI2365EDS-T1-GE3 | ↔ SI2365EDS-T1-GE3 | ⇒ SI2366DS-T1-E3 | ↔ SI2366DS-T1-GE |
| ⊛ SI2366DS-T1-GE3 | ⊣ SI2366DS-T1-GE3 | ⊛ SI2367DS-T1-E3 | D SI2367DS-T1-GE3 | ↔ SI2367DS-T1-GE3 |
| ↔ SI2369DS-T1-GE3 | ⊛ SI2369DS-T1-GE3 | ⊣ SI2371EDS-T1-GE3 | ⊛ SI2371EDS-T1-GE3 | ↔ SI2372DS-T1-E3 |

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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